

Silicon NPN Power Transistors

2SD728

DESCRIPTION

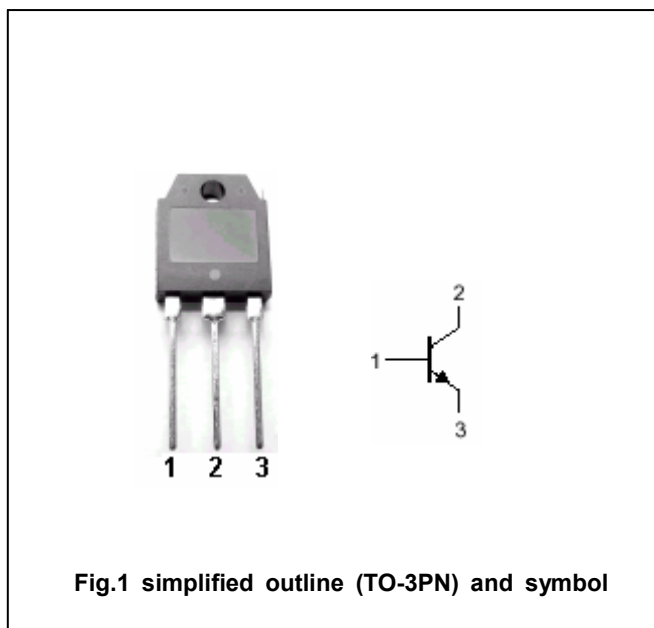
- With TO-3PN package
- Complement to type 2SB692

APPLICATIONS

- For low frequency power amplifier and power switching applications

PINNING

PIN	DESCRIPTION
1	Base
2	Collector;connected to mounting base
3	Emitter

Absolute maximum ratings($T_a=25^\circ\text{C}$)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V_{CBO}	Collector-base voltage	Open emitter	150	V
V_{CEO}	Collector-emitter voltage	Open base	150	V
V_{EBO}	Emitter-base voltage	Open collector	5	V
I_C	Collector current		6	A
P_C	Collector power dissipation	$T_C=25^\circ\text{C}$	70	W
T_j	Junction temperature		150	$^\circ\text{C}$
T_{stg}	Storage temperature		-55~150	$^\circ\text{C}$

Silicon NPN Power Transistors

2SD728

CHARACTERISTICS

Tj=25°C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{(BR)CEO}$	Collector-emitter breakdown voltage	$I_C=50mA ; I_B=0$	150			V
$V_{(BR)EBO}$	Emitter-base breakdown voltage	$I_E=1mA ; I_C=0$	5			V
V_{CEsat}	Collector-emitter saturation voltage	$I_C=5A ; I_B=0.5A$			2.0	V
I_{CBO}	Collector cut-off current	$V_{CB}=150V ; I_E=0$			0.1	mA
I_{EBO}	Emitter cut-off current	$V_{EB}=5V ; I_C=0$			0.1	mA
h_{FE-1}	DC current gain	$I_C=1A ; V_{CE}=5V$	100			
h_{FE-2}	DC current gain	$I_C=5A ; V_{CE}=5V$	20			
f_T	Transition frequency	$I_C=1A ; V_{CE}=5V$		7		MHz
C_{OB}	Collector output capacitance	$I_E=0 ; f=1MHz ; V_{CB}=10V$		160		pF

Silicon NPN Power Transistors

2SD728

PACKAGE OUTLINE

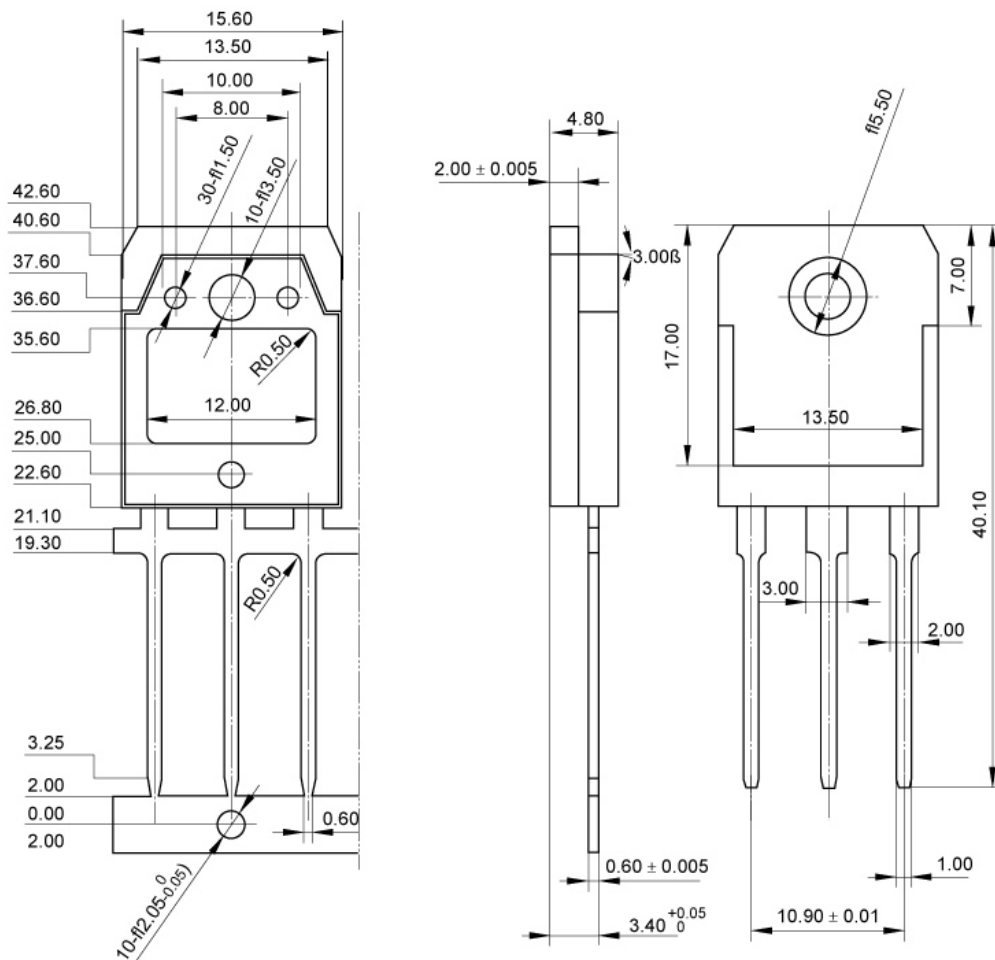


Fig.2 outline dimensions